

ABSTRACT

The present disclosure disclose a gas feeding device and a vapor deposition device. The gas feeding device includes a plurality of gas channels arranged horizontally, provided at a top of the interior of the reaction chamber. Gas inlets of the gas channels are in communication with a gas source group, and gas outlets of the gas channels are spaced apart from the susceptor at different vertical distances. The gas source group includes a gallium source, a nitrogen source, and a dopant gas source. The gallium source and the nitrogen source are in communication with the interior of the reaction chamber via different gas channels, and the dopant gas source is in communication with the interior of the reaction chamber via at least one gas channel, so as to feed a gallium-containing gas, a nitrogen-containing gas, and a dopant gas into the reaction chamber. The gallium-containing gas and the dopant gas fed into the reaction chamber satisfy a preset formula, such that upon the start of feeding the dopant gas into the reaction chamber, the vertical distance to the susceptor is relatively small, so as to increase the concentration of a doping impurity at edges of wafers, thus further ensuring the uniformity of the overall concentration of the doping impurity in the wafers.

(FIG. 1)